



IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Noboru ICHINOSE, et al.

Serial No.: 10/589,852

Group Art Unit: Unknown

Filed: August 17, 006

Examiner: Unknown

For: **METHOD FOR CONTROLLING CONDUCTIVITY OF Ga<sub>2</sub>O<sub>3</sub>  
SINGLE CRYSTAL**

Honorable Commissioner of Patents  
Alexandria, Virginia 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

Under the provisions of 37 CFR §1.97 through §1.98 and pursuant to Applicant's duty of disclosure under 37 CFR §1.56, Applicant respectfully brings the following documents cited in the International Search Report in a counterpart foreign application and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed U.S. Patent Application Publication are not provided in compliance with *Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003*, 1273 Off. Gaz. Pat. Office 55 (August 5, 2003). For the convenience of the Examiner, copies of the first page of the listed U.S. Patent Application Publication are provided.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which Applicant is aware.

In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3) for foreign language documents, Applicant encloses herewith a copy of the International Search

Serial No.: 10/589,852  
Docket No.: PKHF-05004US  
HIR.228

2

Report citing such documents, together with an English-language version (if not already included) of that portion of the Search Report indicating the degree of relevance found by the foreign office.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



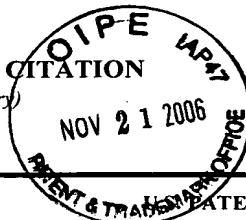
Sean M. McGinn, Esq.  
Registration No. 34,386

Date:

11/21/06  
**MCGINN INTELLECTUAL PROPERTY**  
**LAW GROUP, PLLC**  
8321 Old Courthouse Road, Suite 200  
Vienna, Virginia 22182-3817  
(703) 761-4100  
Customer No. 21254

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional) <b>K06-223706/TBS</b>		Application Number <b>Unknown</b>	
Applicant(s) <b>Joel KUSTER, et al.</b>			
Filing Date <b>Concurrently Herewith</b>		Group Art Unit <b>Unknown</b>	

## PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		<b>2003/0107098</b>	<b>06/12/2003</b>	<b>Ota, et al.</b>			
		<b>2004/0007708</b>	<b>01/15/2004</b>	<b>Inchinose, et al.</b>			

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

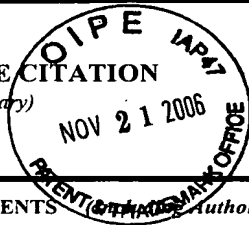
		International Search Report dated April 26, 2005
		Harwig, T. et al., "ELECTRICAL PROPERTIES OF B-Ga2O3 SINGLE CRYSTALS", In: Solid State Communication 1976, Vol. 18, pages 1223 to 1225

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

PKHF-05004 US

Application Number

10/589,852

Applicant(s)

Noboru ICHINOSE

Filing Date

August 17, 2006

Group Art Unit

Not Yet Assigned

\*EXAMINER  
INITIAL

## OTHER DOCUMENTS

(Include Author, Title, Date, Pertinent Pages, Etc.)

UEDA, N. et al., "SYNTHESIS AND CONTROL OF CONDUCTIVITY OF ULTRAVIOLET TRANSMITTING B-Ga<sub>2</sub>O<sub>3</sub> SINGLE CRYSTALS", in: Applied Physics Letters, June, 30, 1997, Vol.70, Issue 26, pages 3561 to 3563

TOMM, Y. et al., " FLOATING ZONE GROWTH OF B-Ga<sub>2</sub>O<sub>3</sub>: A NEW WINDOW MATERIAL FOR OPTOELECTRONIC DEVICE APPLICATIONS", In: Solar Energy Materials & Solar Cells, February, 2001, Vol. 66, pages 369 to 374

FRANK, J. et al., "ELECTRICAL DOPING OF GAS-SENSITIVE, SEMICONDUCTING Ga<sub>2</sub>O<sub>3</sub> THIN FILMS", In: Sensors and Actuators B: Chemical, August 1996, Vol. 34, pages 373 to 377

HARWIG, T. et al., "ELECTRICAL PROPERTIES OF B-Ga<sub>2</sub>O<sub>3</sub> SINGLE CRYSTALS. II", In: Journal of Solid State Chemistry, 15 January, 1978 (15.01.78), Vol. 23, pages 205 to 211

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.